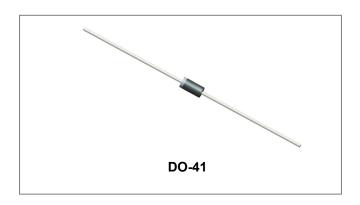






## 11DQ15 SCHOTTKY RECTIFIER



#### **Features**

- · Low profile, axial leaded outline
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Very Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Terminals finish: Tin Lead-free plated
- This is a Pb Free Device
- . All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### **Circuit Diagram**



### **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

### Maximum Ratings(limiting values, T<sub>C</sub> =25°C unless otherwise specified)

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	150	V
Average Forward Current	I <sub>F(AV)</sub>	50% duty cycle @T <sub>L</sub> =75°C, rectangular wave form On PC board 9mm² island	1	А
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3 ms, half Sine pulse	20	Α

#### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@ 1 A, Pulse, T <sub>J</sub> = 25 °C	0.80	0.86	V
-	$V_{F2}$	@ 1 A, Pulse, T <sub>J</sub> = 125 °C	0.65	0.70	V
Reverse Current*	I <sub>R1</sub>	$@V_R = Rated V_R, Pulse, T_J = 25 °C$	0.07	0.5	mA
	I <sub>R2</sub>	$@V_R = Rated V_R, Pulse, T_J = 125 °C$	1.6	10	mA
Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	27	35	PF
Typical Series Inductance	Ls	Measured lead to lead 5 mm from package body	8.0	-	nH
Voltage Rate of Change	dv/dt			10,000	V/μs

<sup>\*</sup> Pulse width < 300 µs, duty cycle < 2%

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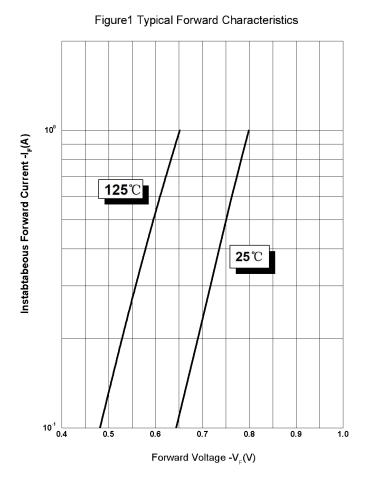


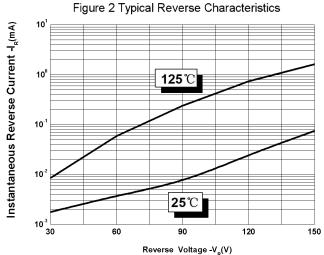


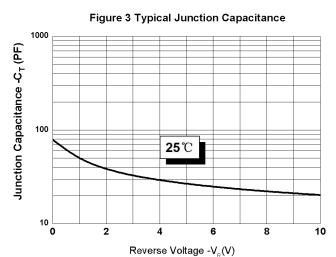
## **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-40 to +175	°C
Storage Temperature	T <sub>stg</sub>	-	-40 to +175	°C
Typical Thermal Resistance Junction to Ambient	R <sub>θJA</sub>	-	100	°C/W
Typical Thermal Resistance Junction to Lead	R <sub>0</sub> JL	-	81	°C/W
Approximate Weight	wt	-	0.34	g

# **Ratings and Characteristics Curves**







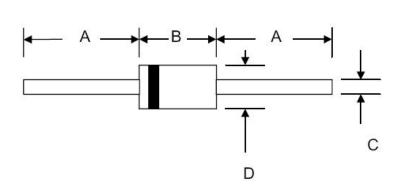
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#### **Mechanical Dimensions DO-41**



CVMPOL	Millimeters		Inches		
SYMBOL	Min.	Max.	Min.	Max.	
А	25.4	-	1.000	-	
В	4.06	5.21	0.160	0.205	
С	0.68	0.864	0.027	0.034	
D	2.00	2.72	0.079	0.107	

## **Ordering Information**

Device	Package	Shipping
11DQ15	DO-41 (Pb-Free)	5000pcs /reel
11DQ15TR	DO-41 (Pb-Free)	5000pcs /reel

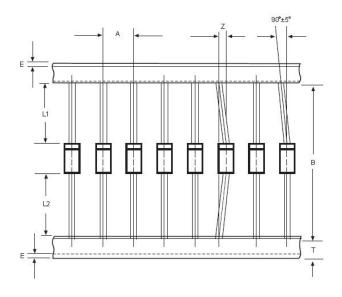
For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

## **Marking Diagram**

Cautions: Molding resin
Epoxy resin UL:94V-0

= Lot Number

# **Carrier Tape Specification DO-41**



SYMBOL	Millimeters		
STWIBOL	Min.	Max.	
А	4.50	5.50	
В	50.9	53.9	
Z	-	1.20	
Т	5.60	6.40	
E	-	0.80	
IL1-L2I	-	1.0	

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